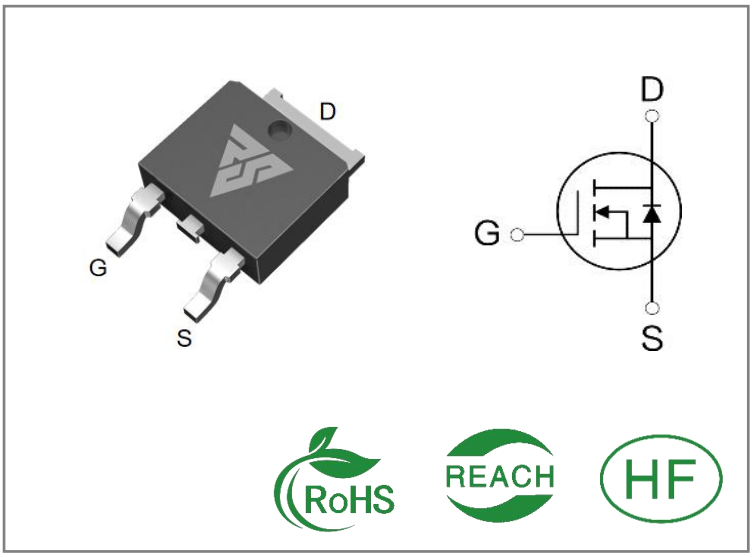
ID	R_{DS}(ON)(Typ)	VDSS
4A	3.2Ω	800V



Applications:

- Switch Mode Power Supply(SMPS)
- Adapter & Charger
- AC-DC Switching Power Supply

Features:

- Fast switching speed
- 100% avalanche tested
- Improved dv/dt capability

Ordering Information

Part Number	Package	Marking	Packing	Qty.
RS4N80D	T0-252	RS4N80D	Tape&reel	2500 PCS

Absolute Maximun Ratings Tc= 2 5℃ unless otherwise specified

Symbol	Parameter	RS4N80D	Units
VDSS	Drain-to-Source Voltage	800	V
ID	Continuous Drain Current TC=25℃	4	A
IDM	Pulsed Drain Current (Note*1)	16	
PD	Power Dissipation	170	W
VGS	Gate- to- Source Voltage	±30	V
EAS	Single Pulse Avalanche Engergy L = 10mH, VDD = 50V, RG = 25 Ω	180	mJ
TL TPKG	Maximum Temperature for Soldering	300	℃
	Leads at 0.063in(1.6mm)from Case for 10 seconds Package Body for 10 seconds	260	
TJ and TSTG	Operating Junction and Storage Temperature Range	-55 to 150	

* Drain Current Limited by Maximum Junction Temperature

Caution: Stresses greater than those listed in the“ Absolute Maximum Ratings” Table may cause permanent damage to the device.

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Thermal Resistance

Symbol	Parameter	RS4N80D	Units	Test Conditions
RθJC	Junction-to-Case	0.7	℃/ W	Drain lead soldered to water cooled heatsink, PD adjusted for a peak junction temperature of + 1 5 0 ℃
RθJA	Junction-to- Ambient	62.5		1 cubic foot chamber,free air.

OFF Characteristics TJ= 25℃ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BVDSS	Drain- to- source Breakdown Voltage	800	--	--	V	VGS=0V,ID=250μA
IDSS	Drain- to- Source Leakage Current	--	--	1	μA	VDS=800V,VGS=0 V
IGSS	Gate- to- Source Forward Leakage	--	--	100	nA	VGS=30V ,VDS=0V
	Gate- to- Source Reverse Leakage	--	--	-100		VGS=-30V ,VDS=0 V

ON Characteristics TJ=25℃ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
RDS(on)	Static Drain- to- Source On-Resistance(Note*2)	--	3.2	3.8	Ω	VGS=10V,ID=2A
VGS(TH)	Gate Threshold Voltage	3	--	4	V	VGS=VDS,ID=250μA

Resistive Switching Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
td(ON)	Turn- on Delay Time	--	34	--	nS	VDS=400V ID=4A RG=25Ω
trise	Rise Time	--	6	--		
td(OFF)	Turn- OFF Delay Time	--	85	--		
tfall	Fall Time	--	25	--		

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Dynamic Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
Ciss	Input Capacitance	--	527	--	pF	VGS=0V VDS=25V f=1.0MHz
Coss	Output Capacitance	--	62	--		
Crss	Reverse Transfer Capacitance	--	12.5	--		
Qg	Total Gate Charge	--	24.5	--	nC	VDS=640V ID=4A VGS=10V
Qgs	Gate- to- Source Charge	--	2.5	--		
Qgd	Gate-to-Drain(" Miller") Charge	--	15.5	--		

Source- Drain Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
IS	Continuous Source Current	--	--	4	A	Integral pn- diode in MOSFET
ISM	Maximum Pulsed Current	--	--	16	A	
VSD	Diode Forward Voltage	--	--	1.4	V	IS=2A,VGS=0V
trr	Reverse Recovery Time	--	445	--	nS	VGS=0V IS=4A, di/dt=100A/μs
Qrr	Reverse Recovery Charge	--	3.1	--	μC	

Notes:

* 1. Repetitive rating, pulse width limited by maximum junction temperature.
* 2. Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 1%

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Typical Feature Curve

Figure 1. Output Characteristics (T_J = 25℃)

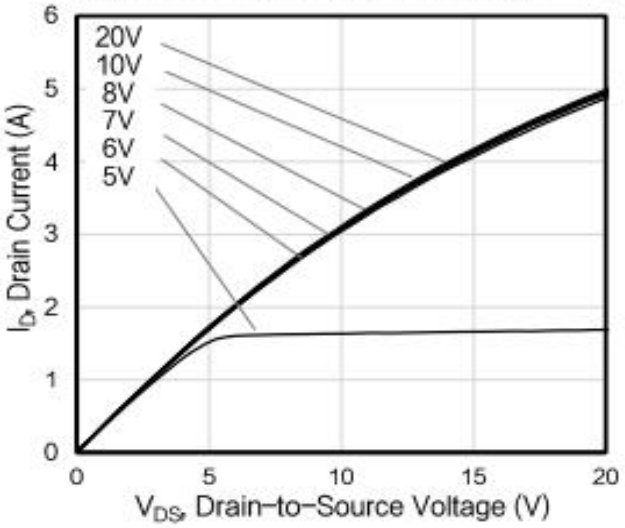

Figure 2. Body Diode Forward Voltage

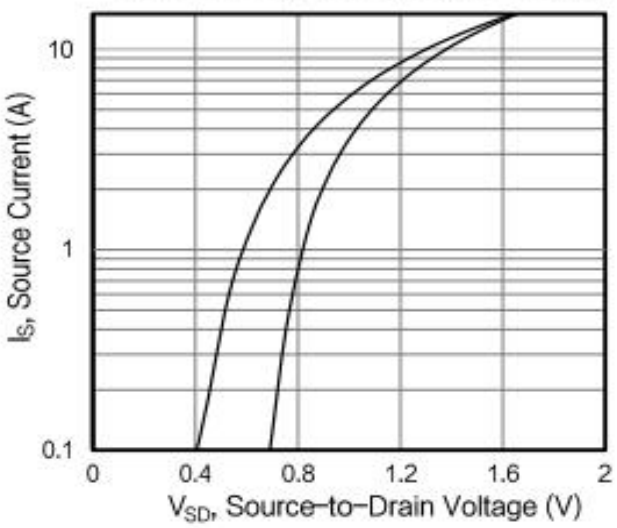

Figure 3. Drain Current vs. Temperature

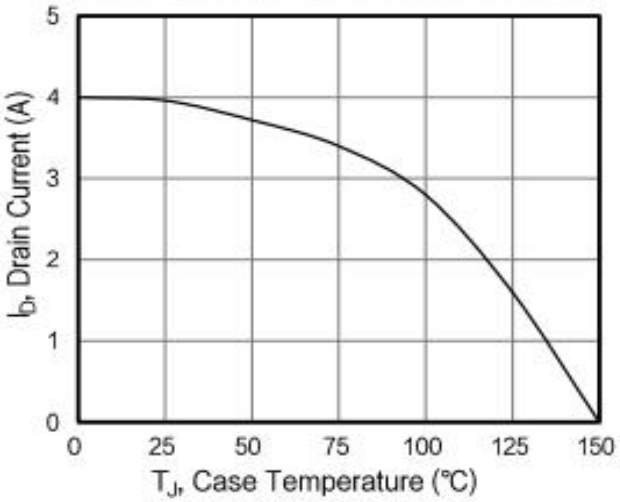

Figure 4. BV_{DSS} Variation vs. Temperature

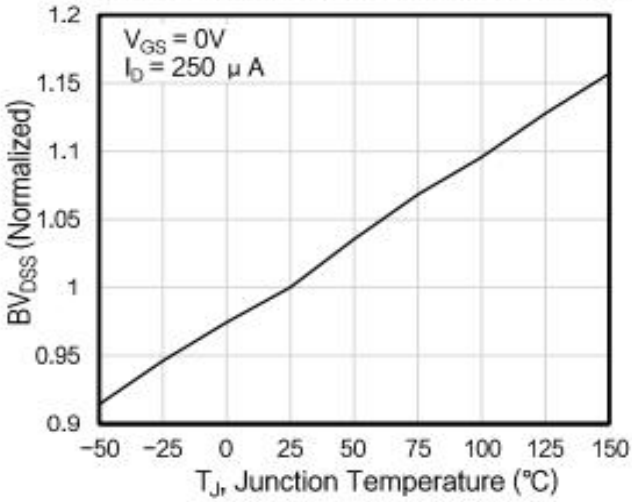

Figure 5. Transfer Characteristics

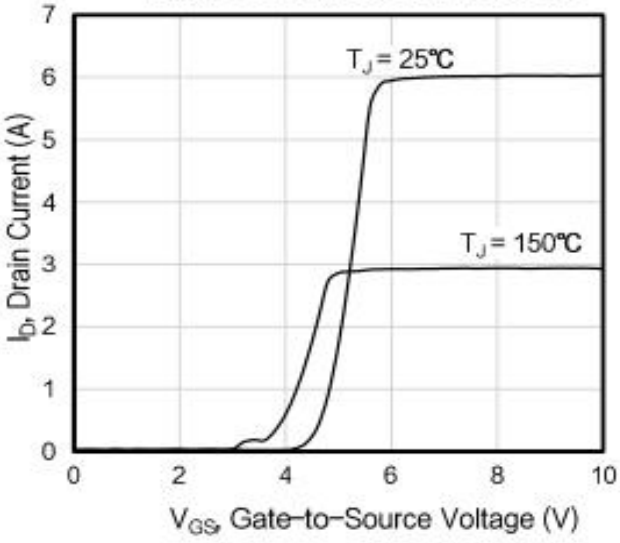

Figure 6. On-Resistance vs. Temperature

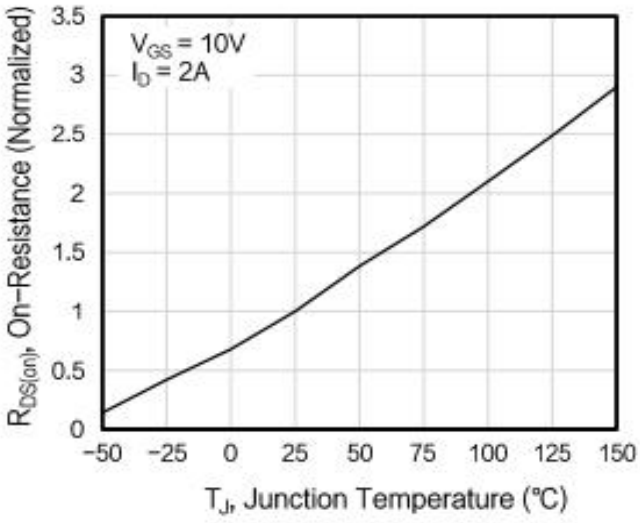

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Figure 7. Capacitance

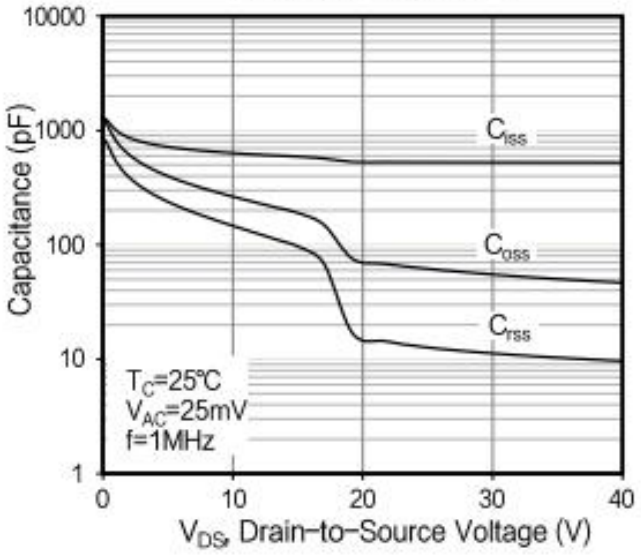


Figure 8. Gate Charge

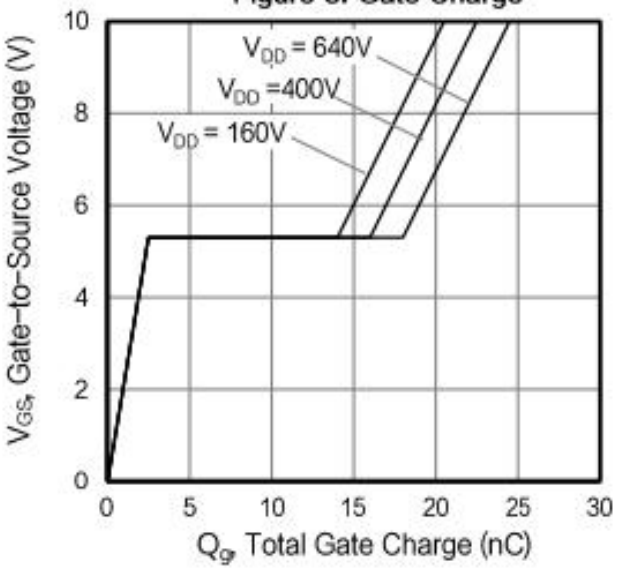
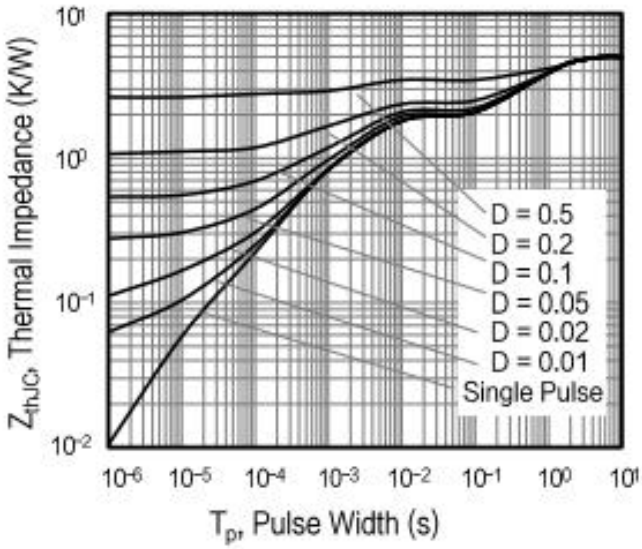


Figure 9. Transient Thermal Impedance



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Test Circuits and Waveforms

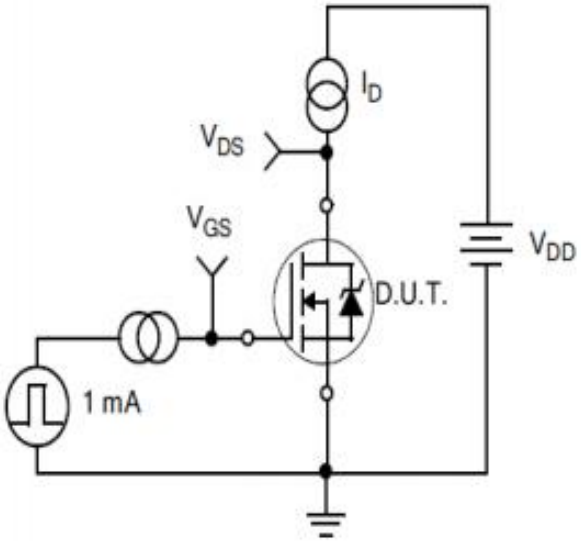

Figure10.
Gate Charge Test Circuit

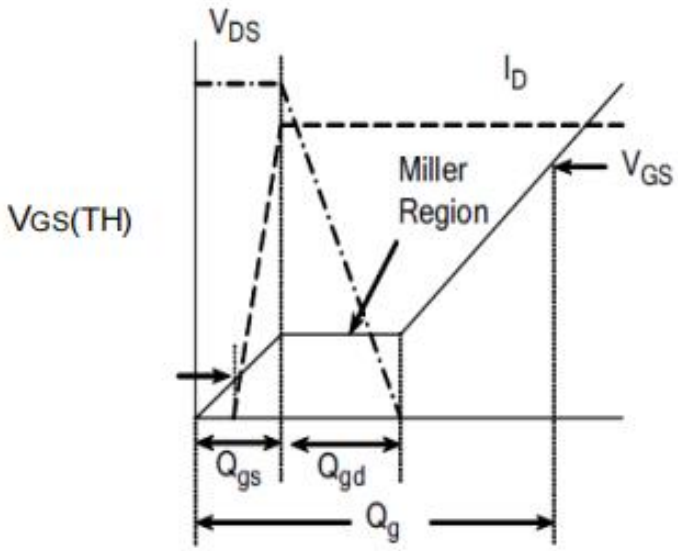

Figure11.
Gate Charge Waveform

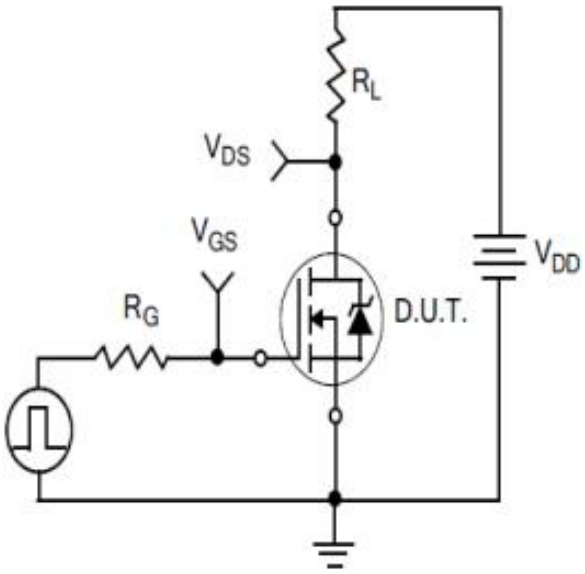

Figure12.
Resistive Switching Test Circuit

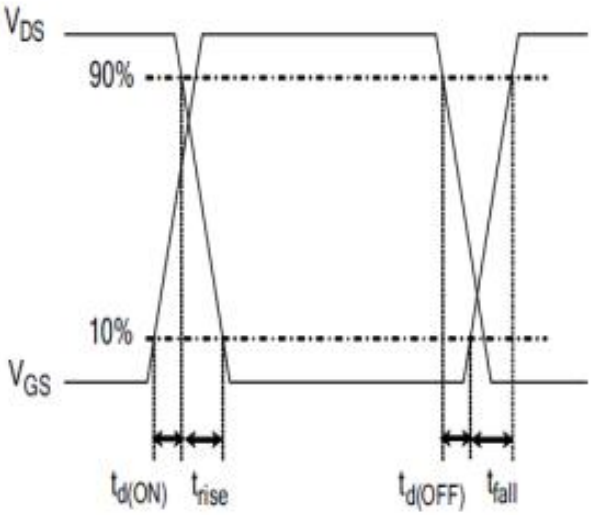

Figure13.
Resistive Switching Waveforms

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Test Circuits and Waveforms

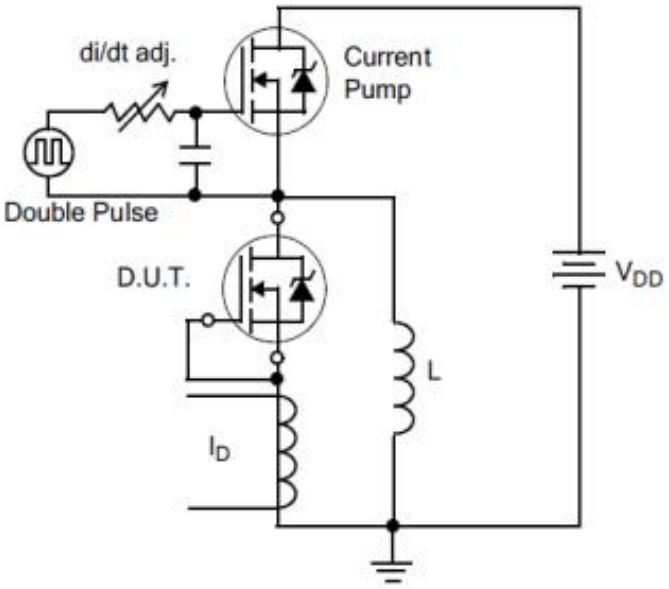


Figure14.Diode Reverse Recovery Test Circuit

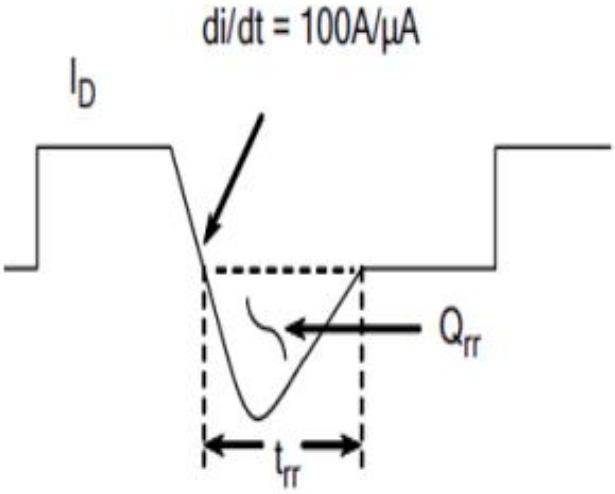


Figure15.Diode Reverse Recovery Waveform

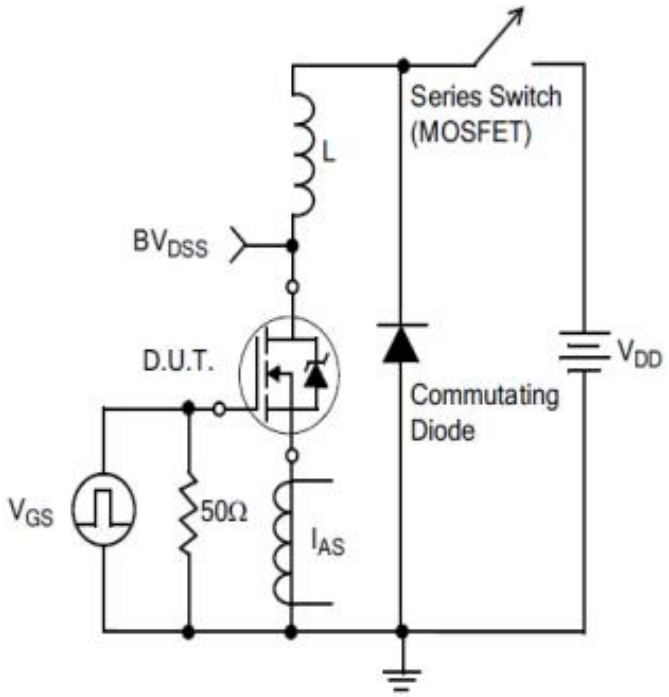
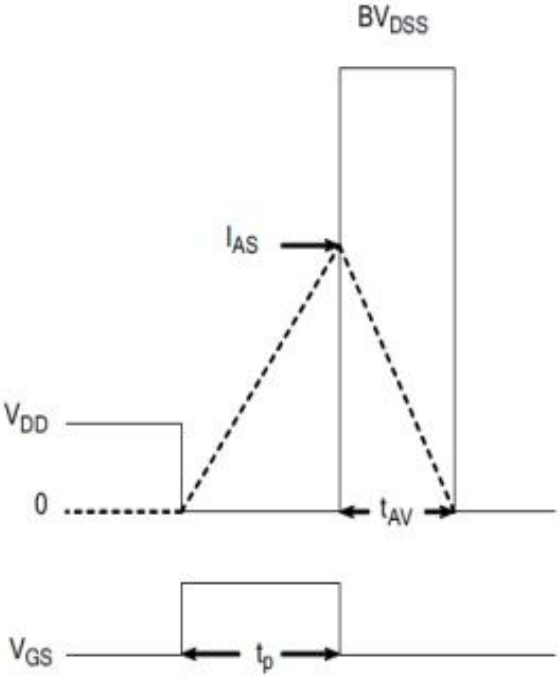


Figure16.Unclamped Inductive Switching Test Circuit



$$E_{AS}=\frac{I_{AS}^2 L}{2}$$

Figure17.Unclamped Inductive Switching Waveforms

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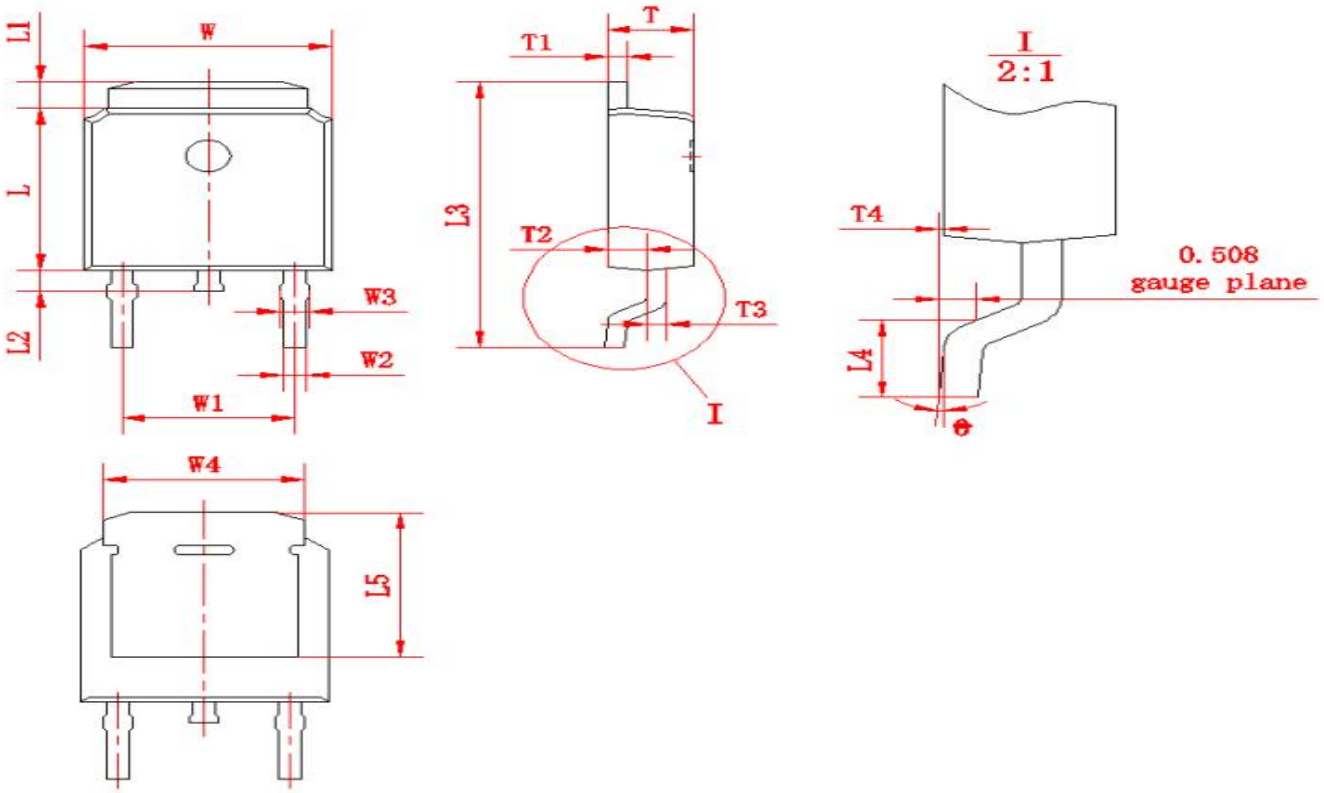
Package outline drawing(TO-252 Unit: mm)



符号	尺寸		符号	尺寸		符号	尺寸	
	Min	Max		Min	Max		Min	Max
W	6.50	6.70	L1	0.80	1.20	T1	0.48	0.58
W1	(4.572)		L2	0.60	1.00	T2	0.95	1.15
W2	0.6	0.8	L3	9.70	10.30	T3	0.48	0.58
W3	0.68	0.88	L4	1.30	1.70	T4	0.00	0.12
W4	(5.3)		L5	(5.20)		0	0	8
L	6.00	6.20	T	2.20	2.40			

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